Supplementary Information

Zeolitic-imidazole framework thin film-based flexible resistive switching memory

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Fig. S1. I-V characteristics for different compliance currents.

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Fig. S2. Schematic illustration of the switching mechanism in ZIF-8 active layer. (a) Electrons are hopping between zinc ions and imidazole molecules. (b) Zinc ions are reduced and delocalized from the original site and electrons are transported through aromatic ring of organic molecules.